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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : TBD
Applicant : Yuichiro Sasaki et al.
Filed : Herewith
Title : "METHOD FOR MAKING JUNCTION AND
PROCESSED MATERIAL FORMED USING THE SAME"

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Examiner : TBD

International App. No. : PCT/JP2004/015308
International Filing Date : October 8, 2004

Customer No. : 52054
Docket No. : 40201

INFORMATION DISCLOSURE STATEMENT

Mail Stop PCT
Commissioner for Patents
P.O. Box 1450
Alexandria, Va. 22313-1450

Sir/Madam:

In accordance with Rule 56, applicants are aware of the publications listed in the International Search Report (ISR, copy enclosed) and in the enclosed copy of Patent Office Form 1449. Copies of the publications cited in the International Search Report are not enclosed as they were previously forwarded by the International Bureau, however, a copy of each publication cited in the specification is enclosed.

If there are any fees required by this communication, please charge such fees to our Deposit Account No. 16-0820, Order No. 40201.

Respectfully submitted,

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By:


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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /GF/

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 40201	SERIAL NO. TBD
INFORMATION DISCLOSURE CITATION BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT: Yuichiro Sasaki et al.	
		FILING DATE: Herewith	GROUP ART UNIT: TBD

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Name	Class	Subclass	Filing Date If Appropriate
	A					
	B					
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FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Subclass	Translation
H	5-206053	08/1993	JAPAN	/	/	Cited on ISR
I	9-17867	01/1997	JAPAN	/	/	Cited on ISR
J	2003-528462	09/2003	JAPAN	/	/	Cited on ISR
K						

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

L	Talwar et al., "Study of Laser Thermal Processing (LPT) to Meet Sub 130 nm Node Shallow Junction Requirements", 2000, pages 175-177 (Cited in Specification)
M	Ito et al., "Flash Lamp Annealing Technology for Ultra-shallow Junction Formation", Extended Abstract of International Workshop on Junction Technology, 2002, pages 23-26 (Cited in Specification)
N	Yamamoto et al., "Impact of Pre-Amorphization for the Reduction of Contact Resistance Using Laser Thermal Process", Extended Abstract of International Workshop on Junction Technology, 2002, pages 27-30 (Cited in Specification)
O	Kagawa et al., "Influence of Pulse Duration on KrF Excimer Laser Annealing Process for Ultra Shallow Junction Formation, Extended Abstract of International Workshop on Junction Technology, 2002, pages 31-34 (Cited in Specification)
P	Ito et al., "Improvement of Threshold Voltage Roll-off by Ultra-shallow Junction Formed by Flash Lamp Annealing", 2003, pages 53-54 (Cited in Specification)

Examiner: /George Fourson/

Date Considered 05/20/2011

*Examiner: Initial if reference considered, regardless of whether citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.